



**CHENMKO ENTERPRISE CO.,LTD**

*Lead free devices*

**SURFACE MOUNT  
PNP Digital Silicon Transistor**

VOLTAGE 50 Volts CURRENT 100 mAmpere

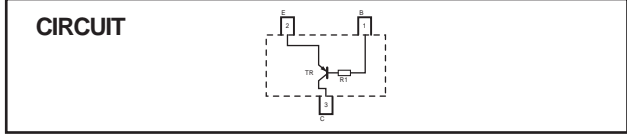
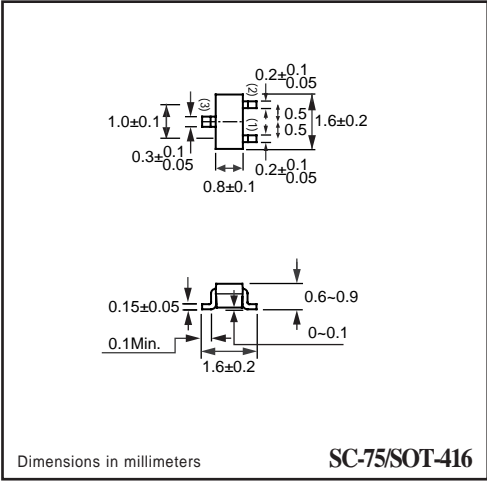
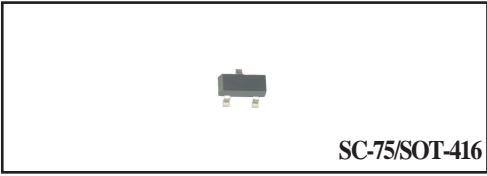
**CHDTA115TEPT**

**APPLICATION**  
\* Switching circuit, Inverter, Interface circuit, Driver circuit.

**FEATURE**  
\* Small surface mounting type. (SC-75/SOT-416)  
\* High current gain.  
\* Suitable for high packing density.  
\* Low collector-emitter saturation.  
\* High saturation current capability.  
\* Internal isolated PNP transistors in one package.  
\* Built in bias resistor(R1=100kΩ, Typ. )

**CONSTRUCTION**  
\* One PNP transistors and bias of thin-film resistors in one package.

**MARKING**  
TE5



**LIMITING VALUES**  
In accordance with the Absolute Maximum Rating System .

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Vcbo	Collector-Base voltage		-50	V
Vceo	Collector-Emitter voltage		-50	V
Vebo	Emitter-Base voltage		-5	V
Ic	Collector current		-100	mA
Pc	Collector Power dissipation	T <sub>amb</sub> ≤ 25 °C, Note 1	150	mW
Tstg	Storage temperature		-55 +150	°C
Tj	Junction temperature		-55 +150	°C
RθJ-s	Thermal resistance , Note 1	junction - soldering point	140	°C/W

**Note**  
1. Transistor mounted on an FR4 printed-circuit board.

## RATING CHARACTERISTIC ( CHDTA115TEPT )

### CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCBO	Collector-Base breakdown voltage	$I_C = -50\mu\text{A}$	-50.0	–	–	V
BVCEO	Collector-Emitter breakdown voltage	$I_C = -1\text{mA}$	-50.0	–	–	V
BVEBO	Emitter-Base breakdown voltage	$I_E = -50\mu\text{A}$	-5.0	–	–	V
$V_{CE(sat)}$	Collector-Emitter Saturation voltage	$I_C = -1\text{mA}; I_B = -0.1\text{mA}$	–	–	-0.3	V
$I_{CBO}$	Collector-Base current	$V_{CB} = -50\text{V}$	–	–	-0.5	$\mu\text{A}$
$I_{EBO}$	Emitter-Base current	$V_{EB} = -4\text{V}$	–	–	-0.5	$\mu\text{A}$
$h_{FE}$	DC current gain	$I_C = -1\text{mA}; V_{CE} = -5.0\text{V}$	100	250	600	
$R_1$	Input resistor		70	100	130	$\text{K}\Omega$
$f_T$	Transition frequency	$I_E = 5\text{mA}, V_{CE} = -10.0\text{V}$ $f = 100\text{MHz}$	–	250	–	MHz

### Note

1. Pulse test:  $t_p \leq 300\mu\text{s}; \delta \leq 0.02$ .